

# **Congratulations to the 30 Newly Elected IEEE Electron Devices Society Fellows**

*Effective January 1, 2018*

Pamela Ann Abshire, Silver Spring, MD, USA  
for contributions to CMOS biosensors

Timothy Boykin, University of Alabama Huntsville, AL, USA  
for contributions to atomistic models for semiconductor device simulation

Jeffrey Calame, Annapolis, MD, USA  
for contributions to high-power microwave and millimeter-wave amplifiers enabled by composite dielectric materials

Kun-yung Chang, Los Altos Hills, CA, USA  
for contributions to transceivers for high-performance networking and high-density memories

Kuan-neng Chen, National Chiao Tung University Hsinchu, Taiwan  
for contributions to 3D integrated circuit and packaging technologies

Akira Fujiwara, NTT Basic Research Laboratories Atsugi, Japan  
for contributions to silicon single-electron devices

Michel Houssa, University of Leuven Leuven, Belgium  
for contributions to materials characterization for advanced MOSFETs

Jaroslav Hyneczek, Allen, TX, USA  
for contributions to solid-state image sensors

Thomas Kazior, Raytheon: Radio Frequency Components Andover, MA, USA  
for leadership in microwave and millimeter wave compound semiconductor technology and heterogeneous integration with silicon

Michael Krames, Philips Lumileds Lighting Company San Jose, CA, USA  
for leadership in GaN-based light-emitting device physics and its commercialization

Isaac Lagnado, San Diego, CA, USA  
for leadership in the development of silicon-on-sapphire technology

Xiaobing Luo, Huazhong University of Science & Technology Wuhan, China  
for contributions to packaging of optoelectronic devices

Chee Wee Liu, National Taiwan University Taipei, Taiwan  
for contributions to high-mobility Ge and SiGe MOSFETs

Ming Liu, Institute of Microelectronics of Chinese Academy of Sciences Beijing, China  
for contributions to the development of resistive non-volatile memories

Wei Lu, University of Michigan Ann Arbor, MI, USA  
for contributions to development of neuromorphic systems

Zhenqiang Ma, University of Wisconsin-Madison Madison, WI, USA

for contributions to flexible and biodegradable microwave electronics

Saibal Mukhopadhyay, Georgia Institute of Technology Atlanta, GA, USA  
for contributions to energy-efficient and robust computing systems design

Hideo Ohno, Tohoku University Sendai, Japan  
for contributions to materials and device design for spintronics

Hidetoshi Onodera, Kyoto University Kyoto, Japan  
for contributions to variation-aware design and analysis of integrated circuits

Philippe Paillet, University of Montpellier-CEA Paris, France  
for contributions to the understanding of radiation effects in electronics

Joseph Pawlowski, Micron Technology, Inc. Boise, ID, USA  
for contributions to memory system interfaces

Seiji Samukawa, Tohoku University Sendai, Japan  
for contributions to damage-free plasma processing for nanodevice manufacturing

Riichiro Shirota, National Chao-Tung University Hsinchu, Taiwan  
for contributions to the development of NAND flash memory

Gregory Snider, University of Notre Dame Notre Dame, IN, USA  
for contributions to single electron based computing technology

Shuji Tanaka, Tohoku University Sendai, Japan  
for contributions to micro-electromechanical systems for acoustic wave devices, physical sensors, and power generation

Victor Veliadis, PowerAmerica Raleigh, NC, USA  
for contributions to development of SiC power devices

Robert Weikle, University of Virginia-Charlottesville Charlottesville, VA, USA  
for contributions to millimeter-wave and submillimeter-wave electronics and instrumentation for terahertz frequencies

Shien-yang Wu, Taiwan Semiconductor Manufacturing Company, Limited Hsinchu, Taiwan  
for leadership in CMOS process integration

Huikai Xie, University of Florida Gainesville, FL, USA  
for contributions to micro-electromechanical optical scanning systems

Jianbin Xu, Chinese University of Hong Kong Shatin NT, Hong Kong  
for contributions to nanoscale electronic materials and devices